

PN EPITAXIAL PLANAR POWER DIODE

CONTACT METALLIZATION

Anode: > 50,000 Å Aluminum

Cathode: Gold

(Polished silicon or "Chrome Nickel Silver" also available)

Also available on:

MOLY PEDESTAL

Size: .140" Diameter (3.56mm)

Thickness: .010" (0.25mm)

BeO PEDESTAL

Size: .142" x .178" (3.61mm x 4.52mm)

Thickness: .023" (0.58mm)

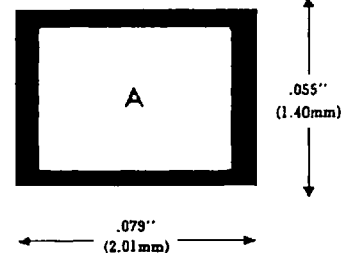
ASSEMBLY RECOMMENDATIONS

It is advisable that:

- the chip be eutectically mounted with gold silicon preform 98/2%.
- 12 mil (0.305mm) aluminum wire be ultrasonically attached to the anode contact.

CHIP NUMBER

501



Anode: .036" x .056" (0.91mm x 1.42mm)

TYPICAL ELECTRICAL CHARACTERISTICS AT 25°C

The following typical electrical characteristics apply for a completely finished component employing the chip number 501 in a DO-4 or equivalent case:

Minimum V_R @ 10 μA	I_R @ 80% V_R	V_F @	I_F	I_F Surge	Maximum t_{rr} @ $I_F = I_R = 1.0A$ $I_{REC} = 0.25A$
> 50V	< 5 μA	1.2V	6.0A	> 100A	200 ns
> 100V	< 5 μA	1.2V	6.0A	> 100A	200 ns
> 300V	< 5 μA	1.2V	6.0A	> 100A	200 ns
> 400V	< 5 μA	1.2V	6.0A	> 100A	450 ns

TYPICAL DEVICE TYPES: 1N3879, 1N3880, 1N3881, 1N3882
 I_F surge $\geq$ 100A.